



## MJ2955

### PNP SILICON POWER TRANSISTORS

The MJ2955 is a silicon Planar Epitaxial NPN transistor in Jedec TO-3 metal case. Designed for general purpose, moderate speed, switching and amplifier applications Compliance to RoHS.

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit	
$V_{CBO}$	Collector to Base Voltage	-100	V	
$V_{CEO}$	#Collector-Emitter Voltage	-60	V	
$V_{CER}$	Collector-Emitter Voltage	-70	V	
$V_{EBO}$	Emitter-Base Voltage	-7	V	
$V_{CB}$	Collector-Base Voltage	-100	V	
$V_{EB}$	Emitter-Base Voltage	-7	V	
$I_C$	Collector Current – Continuous	-15	A	
$I_B$	Base Current – Continuous	-7	A	
$P_D$	Total Device Dissipation	@ $T_C = 25^\circ$	115	W
		Derate above $25^\circ$	0.657	W/°C
$T_J$	Junction Temperature	200	°C	
$T_S$	Storage Temperature	-65 to +200	°C	

#### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJC}$	Thermal Resistance, Junction to Case	1.52	°C/W

## MJ2955

### ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

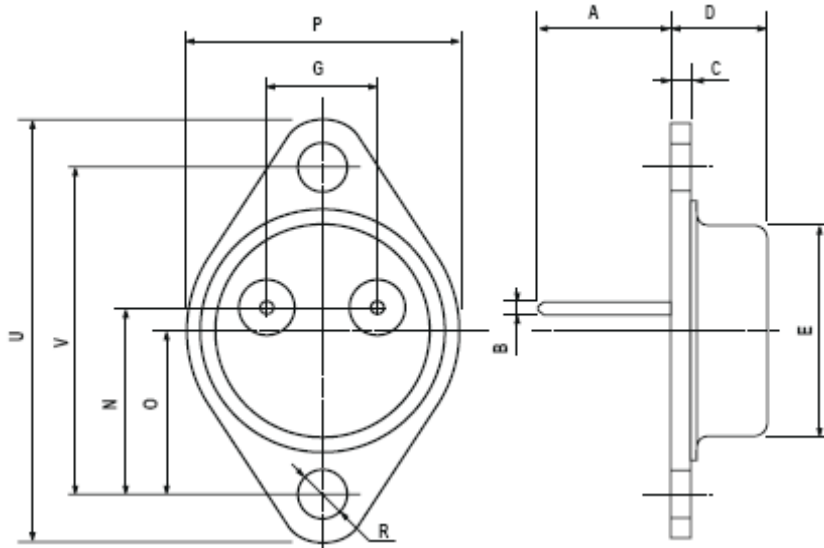
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_C = -200 \text{ mA}, I_B = 0$	-60	-	-	V
$V_{CER}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -200 \text{ mA}, R_{BE} = 100\Omega$	-70	-	-	V
$I_{CEO}$	Collector-Emitter Current	$V_{CE} = -30 \text{ V}, I_B = 0$	-	-	-0.7	mA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = -100 \text{ V}, V_{EB(off)} = -1.5 \text{ V}$	-	-	-1	mA
		$V_{CE} = -100 \text{ V}, V_{EB(off)} = -1.5 \text{ V}$ $T_C = 150 \text{ }^\circ\text{C}$	-	-	-5	
$I_{EBO}$	Emitter Cutoff Current	$V_{BE} = -7 \text{ V}, I_C = 0$	-	-	-5	mA
$h_{FE}$	DC Current Gain	$I_C = -4 \text{ A}, V_{CE} = -4 \text{ A}$	20	-	70	-
		$I_C = -10 \text{ A}, V_{CE} = -4 \text{ A}$	5	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage	$I_C = -4 \text{ A}, I_B = -400 \text{ mA}$	-	-	-1.1	V
		$I_C = -10 \text{ A}, I_B = -3.3 \text{ A}$	-	-	-3	
$V_{BE}$	Base-Emitter Voltage	$I_C = -4 \text{ A}, V_{CE} = -4 \text{ V}$	-	-	-1.5	V
$f_T$	Transition Frequency	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}$ $f = 1 \text{ MHz}$	2.5	-	-	kHz
$I_{s/b}$	Second Breakdown Collector Current	$t = 1 \text{ S (non repetitive)}$	-2.87	-	-	A

In accordance with JEDEC Registration Data  
 (\*) Pulse Width  $\approx 300 \mu\text{s}$ , Duty Cycle  $\angle 2.0\%$

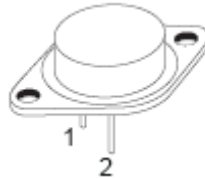
# MJ2955

## MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



Revised October 2014

Information furnished is believed to be accurate and reliable. However, Comset Semiconductors assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. Data are subject to change without notice. Comset Semiconductors makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Comset Semiconductors assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Comset Semiconductors' products are not authorized for use as critical components in life support devices or systems.